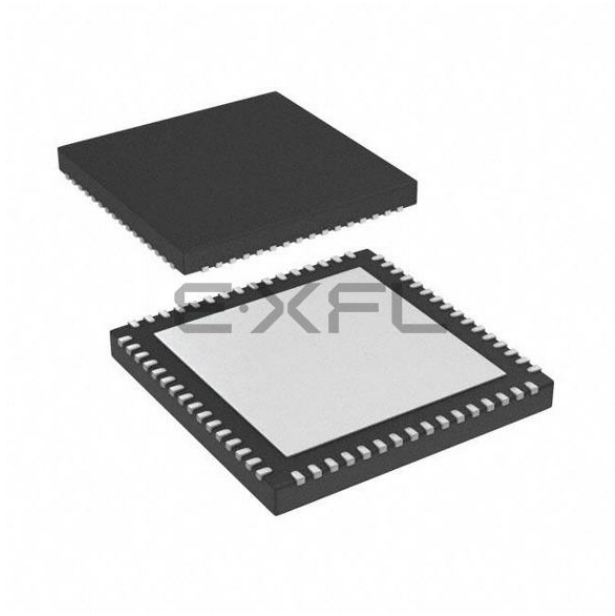
Microchip Technology - PIC24FJ128GB606T-I/MR Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	PIC
Core Size	16-Bit
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, PMP, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, HLVD, POR, PWM, WDT
Number of I/O	53
Program Memory Size	128KB (43K x 24)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic24fj128gb606t-i-mr

4.3.3 READING DATA FROM PROGRAM MEMORY USING EDS

The upper 32 Kbytes of Data Space may optionally be mapped into any 16K word page of the program space. This provides transparent access of stored constant data from the Data Space without the need to use special instructions (i.e., TBLRDL/H).

Program space access through the Data Space occurs when the MSb of EA is '1' and the DSRPAG<9> is also '1'. The lower 8 bits of DSRPAG are concatenated to the Wn<14:0> bits to form a 23-bit EA to access program memory. The DSRPAG<8> decides which word should be addressed; when the bit is '0', the lower word, and when '1', the upper word of the program memory is accessed.

The entire program memory is divided into 512 EDS pages, from 200h to 3FFh, each consisting of 16K words of data. Pages, 200h to 2FFh, correspond to the lower words of the program memory, while 300h to 3FFh correspond to the upper words of the program memory.

Using this EDS technique, the entire program memory can be accessed. Previously, the access to the upper word of the program memory was not supported.

Table 4-15 provides the corresponding 23-bit EDS address for program memory with EDS page and source addresses.

For operations that use PSV and are executed outside a REPEAT loop, the MOV and MOV.D instructions will require one instruction cycle in addition to the specified execution time. All other instructions will require two instruction cycles in addition to the specified execution time.

For operations that use PSV, which are executed inside a REPEAT loop, there will be some instances that require two instruction cycles in addition to the specified execution time of the instruction:

- Execution in the first iteration
- Execution in the last iteration
- Execution prior to exiting the loop due to an interrupt
- Execution upon re-entering the loop after an interrupt is serviced

Any other iteration of the REPEAT loop will allow the instruction accessing data, using PSV, to execute in a single cycle.

TABLE 4-15: EDS PROGRAM ADDRESS WITH DIFFERENT PAGES AND ADDRESSES

DSRPAG (Data Space Read Register)	Source Address while Indirect Addressing	23-Bit EA Pointing to EDS	Comment
200h • • • 2FFh	8000h to FFFFh	000000h to 007FFEh • • • 7F8000h to 7FFFFEh	Lower words of 4M program instructions; (8 Mbytes) for read operations only.
300h • • • 3FFh		000001h to 007FFFh • • • 7F8001h to 7FFFFFh	Upper words of 4M program instructions (4 Mbytes remaining; 4 Mbytes are phantom bytes) for read operations only.
000h		Invalid Address	Address error trap.(1)

Note 1: When the source/destination address is above 8000h and DSRPAG/DSWPAG is '0', an address error trap will occur.

EXAMPLE 4-3: EDS READ CODE FROM PROGRAM MEMORY IN ASSEMBLY

```
; Set the EDS page from where the data to be read
    mov     #0x0202, w0
    mov     w0, DSRPAG                ;page 0x202, consisting lower words, is selected for read
    mov     #0x000A, w1               ;select the location (0x0A) to be read
    bset    w1, #15                   ;set the MSB of the base address, enable EDS mode
;Read a byte from the selected location
    mov.b   [w1++], w2                ;read Low byte
    mov.b   [w1++], w3                ;read High byte
;Read a word from the selected location
    mov     [w1], w2                  ;
;Read Double - word from the selected location
    mov.d   [w1], w2                  ;two word read, stored in w2 and w3
```

6.2 RTSP Operation

The PIC24F Flash program memory array is organized into rows of 128 instructions or 384 bytes. RTSP allows the user to erase blocks of eight rows (1024 instructions) at a time and to program one row at a time. It is also possible to program two instruction word blocks.

The 8-row erase blocks and single row write blocks are edge-aligned, from the beginning of program memory, on boundaries of 3072 bytes and 384 bytes, respectively.

When data is written to program memory using TBLWT instructions, the data is not written directly to memory. Instead, data written using Table Writes is stored in holding latches until the programming sequence is executed.

Any number of TBLWT instructions can be executed and a write will be successfully performed. However, 128 TBLWT instructions are required to write the full row of memory.

To ensure that no data is corrupted during a write, any unused address should be programmed with FFFFFFh. This is because the holding latches reset to an unknown state, so if the addresses are left in the Reset state, they may overwrite the locations on rows which were not rewritten.

The basic sequence for RTSP programming is to set the Table Pointer to point to the programming latches, do a series of TBLWT instructions to load the buffers and set the NVMADRU/NVMADR registers to point to the destination. Programming is performed by setting the control bits in the NVMCON register.

Data can be loaded in any order and the holding registers can be written to multiple times before performing a write operation. Subsequent writes, however, will wipe out any previous writes.

Note:	Writing to a location multiple times without erasing is *not* recommended.

All of the Table Write operations are single-word writes (2 instruction cycles), because only the buffers are written. A programming cycle is required for programming each row.

6.3 JTAG Operation

The PIC24F family supports JTAG boundary scan. Boundary scan can improve the manufacturing process by verifying pin to PCB connectivity.

6.4 Enhanced In-Circuit Serial Programming

Enhanced In-Circuit Serial Programming uses an on-board bootloader, known as the Program Executive (PE), to manage the programming process. Using an SPI data frame format, the Program Executive can erase, program and verify program memory. For more information on Enhanced ICSP, see the device programming specification.

6.5 Control Registers

There are four SFRs used to read and write the program Flash memory: NVMCON, NVMADRU, NVMADR and NVMKEY.

The NVMCON register (Register 6-1) controls which blocks are to be erased, which memory type is to be programmed and when the programming cycle starts.

NVMKEY is a write-only register that is used for write protection. To start a programming or erase sequence, the user must consecutively write 55h and AAh to the NVMKEY register. Refer to **Section 6.6 "Programming Operations"** for further details.

The NVMADRU/NVMADR registers contain the upper byte and lower word of the destination of the NVM write or erase operation. Some operations (chip erase, Inactive Partition erase) operate on fixed locations and do not require an address value.

6.6 Programming Operations

A complete programming sequence is necessary for programming or erasing the internal Flash in RTSP mode. During a programming or erase operation, the processor stalls (waits) until the operation is finished. Setting the WR bit (NVMCON<15>) starts the operation and the WR bit is automatically cleared when the operation is finished.

In Dual Partition mode, programming or erasing the Inactive Partition will not stall the processor; the code in the Active Partition will still execute during the programming operation.

It is important to mask interrupts for a minimum of 5 instruction cycles during Flash programming. This can be done in Assembly using the DISI instruction (see Example 6-1).

REGISTER 8-5: INTCON4: INTERRUPT CONTROL REGISTER 4

U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0
—	—	—	—	—	—	—	—
bit 15							bit 8

U-0	U-0	U-0	U-0	U-0	U-0	R/C-0	R/C-0
—	—	—	—	—	—	ECCDBE	SGHT
bit 7							bit 0

Legend:	C = Clearable bit		
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as ‘0’	
-n = Value at POR	‘1’ = Bit is set	‘0’ = Bit is cleared	x = Bit is unknown

bit 15-2 **Unimplemented:** Read as ‘0’

bit 1 **ECCDBE:** ECC Double-Bit Error Trap bit
1 = ECC Double-Bit Error trap has occurred
0 = ECC Double-Bit Error trap has not occurred

bit 0 **SGHT:** Software Generated Hard Trap Status bit
1 = Software generated hard trap has occurred
0 = Software generated hard trap has not occurred

REGISTER 9-3: OSCTUN: FRC OSCILLATOR TUNE REGISTER

R/W-0	U-0	R/W-0	R/W-1	R-0	R/W-0	R-0	R/W-0
STEN	—	STSIDL	STSRC(1)	STLOCK	STLPOL	STOR	STORPOL
bit 15							bit 8

U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0
—	—	TUN5(2)	TUN4(2)	TUN3(2)	TUN2(2)	TUN1(2)	TUN0(2)
bit 7							bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 15 **STEN:** FRC Self-Tune Enable bit
1 = FRC self-tuning is enabled; TUNx bits are controlled by hardware
0 = FRC self-tuning is disabled; application may optionally control the TUNx bits

bit 14 **Unimplemented:** Read as '0'

bit 13 **STSIDL:** FRC Self-Tune Stop in Idle bit
1 = Self-tuning stops during Idle mode
0 = Self-tuning continues during Idle mode

bit 12 **STSRC:** FRC Self-Tune Reference Clock Source bit(1)
1 = FRC is tuned to approximately match the USB host clock tolerance
0 = FRC is tuned to approximately match the 32.768 kHz SOSC tolerance

bit 11 **STLOCK:** FRC Self-Tune Lock Status bit
1 = FRC accuracy is currently within ±0.2% of the STSRC reference accuracy
0 = FRC accuracy may not be within ±0.2% of the STSRC reference accuracy

bit 10 **STLPOL:** FRC Self-Tune Lock Interrupt Polarity bit
1 = A self-tune lock interrupt is generated when STLOCK is '0'
0 = A self-tune lock interrupt is generated when STLOCK is '1'

bit 9 **STOR:** FRC Self-Tune Out of Range Status bit
1 = STSRC reference clock error is beyond the range of TUN<5:0>; no tuning is performed
0 = STSRC reference clock is within the tunable range; tuning is performed

bit 8 **STORPOL:** FRC Self-Tune Out of Range Interrupt Polarity bit
1 = A self-tune out of range interrupt is generated when STOR is '0'
0 = A self-tune out of range interrupt is generated when STOR is '1'

bit 7-6 **Unimplemented:** Read as '0'

bit 5-0 **TUN<5:0>:** FRC Oscillator Tuning bits(2)
011111 = Maximum frequency deviation
011110 =
• • •
000001 =
000000 = Center frequency, oscillator is running at factory calibrated frequency
111111 =
• • •
100001 =
100000 = Minimum frequency deviation

Note 1: Use of either clock tuning reference source has specific application requirements. See **Section 9.5 "FRC Active Clock Tuning"** for details.

2: These bits are read-only when STEN = 1.

REGISTER 9-7: OSCFDIV: OSCILLATOR FRACTIONAL DIVISOR REGISTER(1)

R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0
TRIM<0:7>							
bit 15							bit 8

R/W-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0
TRIM8	—	—	—	—	—	—	—
bit 7							bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 15-7 **TRIM<0:8>:** Trim bits

Provides fractional additive to the DIV<14:0> value for the 1/2 period of the oscillator clock.
0000_0000_0 = 0/512 (0.0) divisor added to DIVx value
0000_0000_1 = 1/512 (0.001953125) divisor added to DIVx value
0000_0001_0 = 2/512 (0.00390625) divisor added to DIVx value
•
•
•
100000000 = 256/512 (0.5000) divisor added to DIVx value
•
•
•
1111_1111_0 = 510/512 (0.99609375) divisor added to DIVx value
1111_1111_1 = 511/512 (0.998046875) divisor added to DIVx value

bit 6-0 **Unimplemented:** Read as '0'

Note 1: TRIMx values greater than zero are ONLY valid when DIVx values are greater than zero.

REGISTER 10-5: PMD5: PERIPHERAL MODULE DISABLE REGISTER 5

U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0
—	—	—	—	—	—	—	—
bit 15							bit 8

U-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0
—	CCP7MD	CCP6MD	CCP5MD	CCP4MD	CCP3MD	CCP2MD	CCP1MD
bit 7							bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 15-7 **Unimplemented:** Read as '0'

bit 6 **CCP7MD:** SCCP7 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

bit 5 **CCP6MD:** SCCP6 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

bit 4 **CCP5MD:** SCCP5 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

bit 3 **CCP4MD:** MCCP4 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

bit 2 **CCP3MD:** MCCP3 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

bit 1 **CCP2MD:** MCCP2 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

bit 0 **CCP1MD:** MCCP1 Module Disable bit
1 = Module is disabled
0 = Module power and clock sources are enabled

NOTES:

REGISTER 20-2: BDnSTAT: BUFFER DESCRIPTOR n STATUS REGISTER PROTOTYPE, CPU MODE (BD0STAT THROUGH BD63STAT)

R/W-x	R/W-x	r-0	r-0	R/W-x	R/W-x	R/W-x, HSC	R/W-x, HSC
UOWN	DTS(1)	—	—	DTSEN	BSTALL	BC9	BC8
bit 15							bit 8

R/W-x, HSC	R/W-x, HSC	R/W-x, HSC	R/W-x, HSC	R/W-x, HSC	R/W-x, HSC	R/W-x, HSC	R/W-x, HSC
BC7	BC6	BC5	BC4	BC3	BC2	BC1	BC0
bit 7							bit 0

Legend:	r = Reserved bit	HSC = Hardware Settable/Clearable bit	
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'r' = Reserved bit	x = Bit is unknown

bit 15 **UOWN:** USB Own bit
- 0 = The microcontroller core owns the BD and its corresponding buffer; the USB module ignores all other fields in the BD

bit 14 **DTS:** Data Toggle Packet bit(1)
- 1 = Data 1 packet
- 0 = Data 0 packet

bit 13-12 **Reserved:** Maintain as '0'

bit 11 **DTSEN:** Data Toggle Synchronization Enable bit
- 1 = Data toggle synchronization is enabled; data packets with incorrect Sync value will be ignored
- 0 = No data toggle synchronization is performed

bit 10 **BSTALL:** Buffer STALL Enable bit
- 1 = Buffer STALL is enabled; STALL handshake issued if a token is received that would use the BD in the given location (UOWN bit remains set, BD value is unchanged); corresponding EPSTALL bit will get set on any STALL handshake
- 0 = Buffer STALL is disabled

bit 9-0 **BC<9:0>:** Byte Count bits

This represents the number of bytes to be transmitted or the maximum number of bytes to be received during a transfer. Upon completion, the byte count is updated by the USB module with the actual number of bytes transmitted or received.

Note 1: This bit is ignored unless DTSEN = 1.

NOTES:

25.4 Achieving Maximum A/D Converter (ADC) Performance

In order to get the shortest overall conversion time (called the "throughput") while maintaining accuracy, several factors must be considered. These are described in detail below.

- Dependence of AVDD – If the AVDD supply is < 2.7V, the Charge Pump Enable bit (PUMPEN, AD1CON3<13>) should be set to '1'. The input channel multiplexer has a varying resistance with AVDD (the lower AVDD, the higher the internal switch resistance). The charge pump provides a higher internal AVDD to keep the switch resistance as low as possible.
- Dependence on TAD – The ADC timing is driven by TAD, not TCYC. Selecting the TAD time correctly is critical to getting the best ADC throughput. It is important to note that the overall ADC throughput is not simply the 'Conversion Time' of the SAR; it is the combination of the Conversion Time, the Sample Time and additional TAD delays for internal synchronization logic.
- Relationship between TCYC and TAD – There is not a fixed 1:1 timing relationship between TCYC and TAD. The fastest possible throughput is fundamentally set by TAD (min), not by TCYC. The TAD time is set as a programmable integer multiple of TCYC by the ADCS<7:0> bits. Referring to Table 33-26, the TAD (min) time is greater than the 4 MHz period of the dedicated ADC RC clock generator. Therefore, TAD must be 2 TCYC in order to use the RC clock for fastest throughput. The TAD (min) is a multiple of 3.597 MHz as opposed to 4 MHz. To run as fast as possible, TCYC must be a multiple of TAD (min) because values of ADCSx are integers. For example, if a standard "color burst" crystal of 14.31818 MHz is used, TCYC is 279.4 ns, which is very close to TAD (min) and the ADC throughput is optimal. Running at 16 MHz will actually reduce the throughput, because TAD will have to be 500 ns as the TCYC of 250 ns violates TAD (min).
- Dependence on driving Source Resistance (RS) – Certain transducers have high output impedance (> 2.5 kΩ). Having a high RS will require longer sampling time to charge the S/H capacitor through the resistance path (see Figure 25-3). The worst case scenario is a full-range voltage step of AVSS to AVDD, with the sampling cap at AVSS. The capacitor time constant is (RS + RIC + RSS) (CHOLD) and the sample time needs to be 6 time constants minimum (8 preferred). Since the ADC logic timing is TAD-based, the sample time (in TAD) must be long enough, over all conditions, to charge/discharge CHOLD. Do not assume one TAD is sufficient sample time; longer times may be required to achieve the accuracy needed by the application. The value of CHOLD is 40 pF.

A small amount of charge is present at the ADC input pin when the sample switch is closed. If RS is high, this will generate a DC error exceeding 1 LSB. Keeping RS < 50Ω is recommenced for best results. The error can also be reduced by increasing sample time (a 2 kΩ value of RS requires a 3 µS sample time to eliminate the error).

- Calculating Throughput – The throughput of the ADC is based on TAD. The throughput is given by:

$$Throughput = \left(\frac{1}{Sample\ Time + SAR\ Conversion\ Time + Clock\ Sync\ Time}\right)$$

where:

Sample Time is the calculated TAD periods for the application.

SAR Conversion Time is 12 TAD for 10-bit and 14 TAD for 12-bit conversions.

Clock Sync Time is 2.5 TAD (worst case scenario).

For example, using an 8 MHz FRC means the TCYC = 250 ns. This requires: TAD = 2 TCYC = 500 ns. Therefore, the throughput is:

$$Throughput = \left(\frac{1}{500\ ns + 14 \cdot 500\ ns + 2.5 \cdot 500\ ns}\right) = 114.28\ KS/sec$$

Note that the clock sync delay could be as little as 1.5 TAD, which could produce 121 KS/sec, but that cannot be ensured as the timing relationship is asynchronous and not specified. The worst case timing of 2.5 TAD should be used to calculate throughput.

For example, if a certain transducer has a 20 kΩ output impedance, the maximum sample time is determined by:

$$Sample\ Time = 6 \cdot (RS + RIC + RSS) \cdot CHOLD$$
$$= 6 \cdot (20K + 250 + 350) \cdot 40\ pF$$
$$= 4.95\ \mu S$$

If TAD = 500 ns, this requires a Sample Time of 4.95 us/ 500 ns = 10 TAD (for a full-step voltage on the transducer output).

REGISTER 25-5: AD1CON5: A/D CONTROL REGISTER 5

R/W-0	R/W-0	R/W-0	R/W-0	U-0	U-0	R/W-0	R/W-0
ASEN	LPEN	CTMREQ	BGREQ	—	—	ASINT1	ASINT0
bit 15							bit 8

U-0	U-0	U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0
—	—	—	—	WM1	WM0	CM1	CM0
bit 7							bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 15 **ASEN:** Auto-Scan Enable bit
1 = Auto-scan is enabled
0 = Auto-scan is disabled

bit 14 **LPEN:** Low-Power Enable bit
1 = Low power is enabled after scan
0 = Full power is enabled after scan

bit 13 **CTMREQ:** CTMU Request bit
1 = CTMU is enabled when the A/D is enabled and active
0 = CTMU is not enabled by the A/D

bit 12 **BGREQ:** Band Gap Request bit
1 = Band gap is enabled when the A/D is enabled and active
0 = Band gap is not enabled by the A/D

bit 11-10 **Unimplemented:** Read as '0'

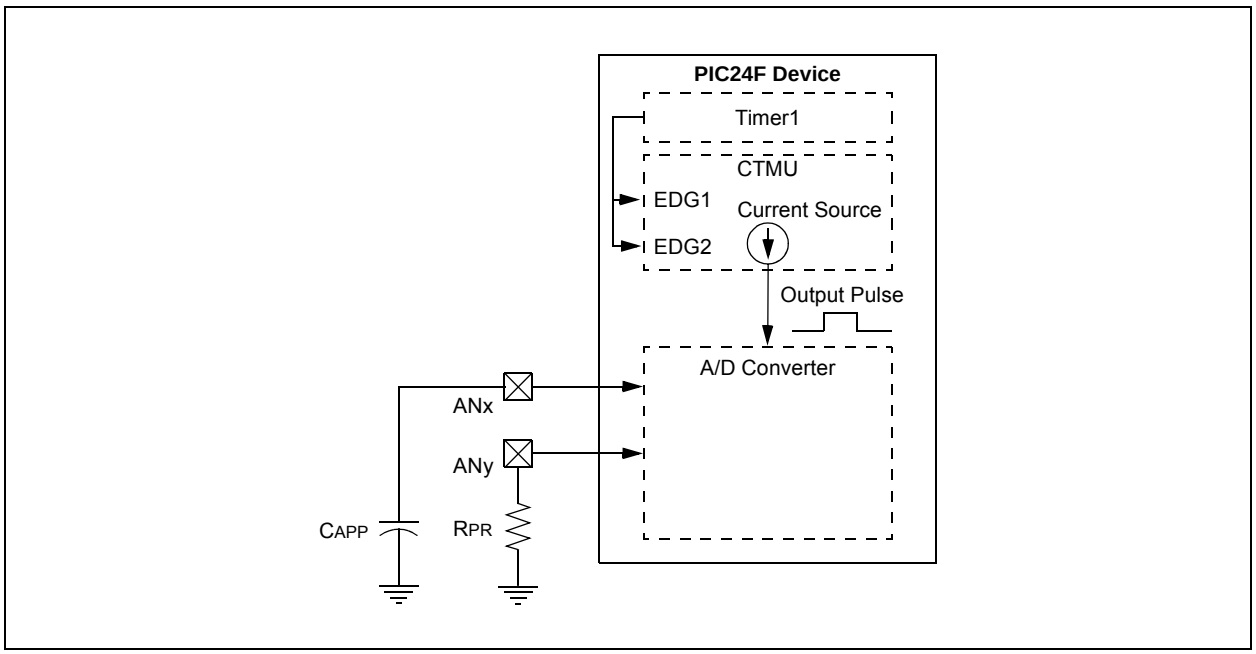
bit 9-8 **ASINT<1:0>:** Auto-Scan (Threshold Detect) Interrupt Mode bits
11 = Interrupt after Threshold Detect sequence has completed and valid compare has occurred
10 = Interrupt after valid compare has occurred
01 = Interrupt after Threshold Detect sequence has completed
00 = No interrupt

bit 7-4 **Unimplemented:** Read as '0'

bit 3-2 **WM<1:0>:** Write Mode bits
11 = Reserved
10 = Auto-compare only (conversion results are not saved, but interrupts are generated when a valid match occurs, as defined by the CMx and ASINTx bits)
01 = Convert and save (conversion results are saved to locations as determined by the register bits when a match occurs, as defined by the CMx bits)
00 = Legacy operation (conversion data is saved to a location determined by the Buffer register bits)

bit 1-0 **CM<1:0>:** Compare Mode bits
11 = Outside Window mode: Valid match occurs if the conversion result is outside of the window defined by the corresponding buffer pair
10 = Inside Window mode: Valid match occurs if the conversion result is inside the window defined by the corresponding buffer pair
01 = Greater Than mode: Valid match occurs if the result is greater than the value in the corresponding Buffer register
00 = Less Than mode: Valid match occurs if the result is less than the value in the corresponding Buffer register

FIGURE 28-1: TYPICAL CONNECTIONS AND INTERNAL CONFIGURATION FOR CAPACITANCE MEASUREMENT



28.2 Measuring Time/Routing Current Source to A/D Input Pin

Time measurements on the pulse width can be similarly performed using the A/D module's Internal Capacitor (CAD) and a precision resistor for current calibration. Figure 28-2 displays the external connections used for time measurements, and how the CTMU and A/D modules are related in this application. This example also shows both edge events coming from the external CTEDx pins, but other configurations using internal edge sources are possible.

This mode is enabled by clearing the TGEN bit (CTMUCON1L<12>). The current source is tied to the input of the A/D after the sampling switch. Therefore, the A/D bit, SAMP, must be set to '1' in order for the current to be routed through the channel selection MUX to the desired pin.

28.3 Pulse Generation and Delay

The CTMU module can also generate an output pulse with edges that are not synchronous with the device's system clock. More specifically, it can generate a pulse with a programmable delay from an edge event input to the module.

When the module is configured for pulse generation delay by setting the TGEN bit (CTMUCON1<12>), the internal current source is connected to the B input of Comparator 2. A Capacitor (CDELAY) is connected to the Comparator 2 pin, C2INB, and the Comparator Voltage Reference, CVREF, is connected to C2INA. CVREF is then configured for a specific trip point. The module begins to charge CDELAY when an edge event is detected. When CDELAY charges above the CVREF trip point, a pulse is output on CTPLS. The length of the pulse delay is determined by the value of CDELAY and the CVREF trip point.

Figure 28-3 illustrates the external connections for pulse generation, as well as the relationship of the different analog modules required. While CTED1 is shown as the input pulse source, other options are available. A detailed discussion on pulse generation with the CTMU module is provided in the *"dsPIC33/PIC24 Family Reference Manual"*.

NOTES:

REGISTER 30-11: FDEVOPT1 CONFIGURATION REGISTER

U-1	U-1	U-1	U-1	U-1	U-1	U-1	U-1
—	—	—	—	—	—	—	—
bit 23							bit 16

U-1	U-1	U-1	U-1	U-1	U-1	U-1	U-1
—	—	—	—	—	—	—	—
bit 15							bit 8

U-1	U-1	U-1	R/PO-1	R/PO-1	R/PO-1	R/PO-1	U-1
—	—	—	ALTVREF	SOSCHP(1)	TMPRPIN	ALTCMPI	—
bit 7							bit 0

Legend:	PO = Program Once bit		
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '1'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 23-5 **Unimplemented:** Read as '1'

bit 4 **ALTVREF:** Alternate Voltage Reference Location Enable bit (100-pin and 121-pin devices only)
1 = VREF+ and CVREF+ on RA10, VREF- and CVREF- on RA9
0 = VREF+ and CVREF+ on RB0, VREF- and CVREF- on RB1

bit 3 **SOSCHP:** SOSC High-Power Enable bit (valid only when SOSCSEL = 1)(1)
1 = SOSC High-Power mode is enabled
0 = SOSC Low-Power mode is enabled

bit 2 **TMPRPIN:** Tamper Pin Enable bit
1 = $\overline{\text{TMPR}}$ pin function is disabled
0 = $\overline{\text{TMPR}}$ pin function is enabled

bit 1 **ALTCMPI:** Alternate Comparator Input Enable bit
1 = C1INC, C2INC and C3INC are on their standard pin locations
0 = C1INC, C2INC and C3INC are on RG9

bit 0 **Unimplemented:** Read as '1'

Note 1: High-Power mode is for crystals with 35K ESR (typical). Low-Power mode is for crystals with more than 65K ESR.

NOTES:

TABLE 33-3: DC CHARACTERISTICS: TEMPERATURE AND VOLTAGE SPECIFICATIONS

DC CHARACTERISTICS			Standard Operating Conditions: 2.0V to 3.6V (unless otherwise stated) Operating temperature -40°C ≤ TA ≤ +85°C for Industrial				
Param No.	**Symbol**	**Characteristic**	**Min**	**Typ**	**Max**	**Units**	**Conditions**
Operating Voltage							
DC10	VDD	**Supply Voltage**	2.0	—	3.6	V	BOR is disabled
			VBOR	—	3.6	V	BOR is enabled
DC12	VDR	**RAM Data Retention Voltage(1)**	Greater of: VPORREL or VBOR	—	—	V	VBOR is used only if BOR is enabled (BOREN = 1)
DC16	VPOR	**VDD Start Voltage** to Ensure Internal Power-on Reset Signal	VSS	—	—	V	**(Note 2)**
DC17A	SVDD	**Recommended VDD Rise Rate** to Ensure Internal Power-on Reset Signal	1V/20 ms	—	1V/10 µS	sec	**(Note 2, Note 4)**
DC17B	VBOR	**Brown-out Reset Voltage** on VDD Transition, High-to-Low	2.0	2.1	2.2	V	**(Note 3)**

Note 1: This is the limit to which VDD may be lowered and the RAM contents will always be retained.

2: If the VPOR or SVDD parameters are not met, or the application experiences slow power-down VDD ramp rates, it is recommended to enable and use BOR.

3: On a rising VDD power-up sequence, application firmware execution begins at the higher of the VPORREL or VBOR level (when BOREN = 1).

4: VDD rise times outside this window may not internally reset the processor and are not parametrically tested.

33.2 AC Characteristics and Timing Parameters

The information contained in this section defines the PIC24FJ1024GA610/GB610 family AC characteristics and timing parameters.

TABLE 33-16: TEMPERATURE AND VOLTAGE SPECIFICATIONS – AC

AC CHARACTERISTICS	**Standard Operating Conditions: 2.0V to 3.6V (unless otherwise stated)** Operating temperature -40°C ≤ TA ≤ +85°C for Industrial Operating voltage VDD range as described in **Section 33.1 "DC Characteristics"**.

FIGURE 33-2: LOAD CONDITIONS FOR DEVICE TIMING SPECIFICATIONS

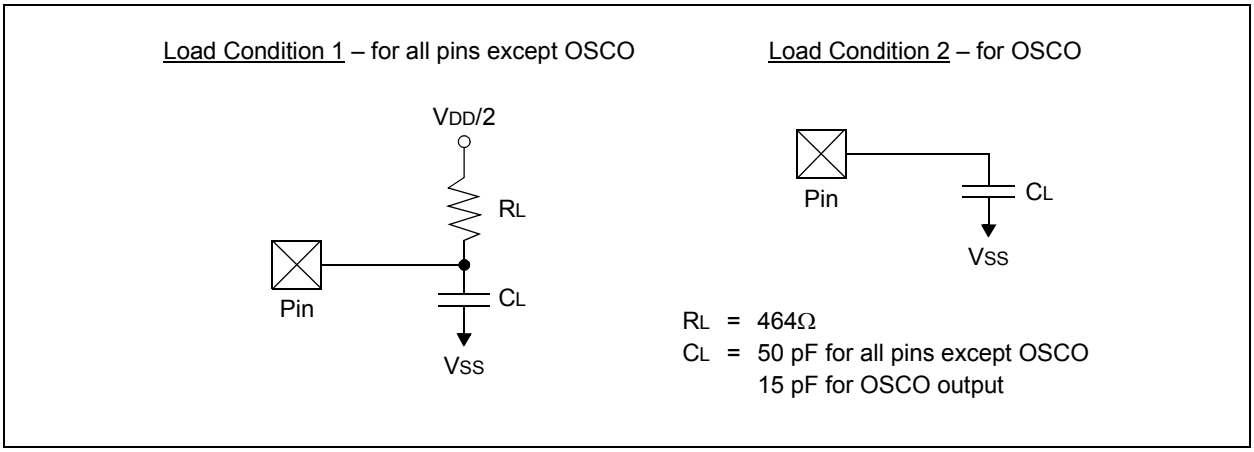


TABLE 33-17: CAPACITIVE LOADING REQUIREMENTS ON OUTPUT PINS

Param No.	Symbol	Characteristic	Min	Typ(1)	Max	Units	Conditions
DO50	COSCO	OSCO/CLKO Pin	—	—	15	pF	In XT and HS modes when external clock is used to drive OSCI
DO56	CIO	All I/O Pins and OSCO	—	—	50	pF	EC mode
DO58	CB	SCLx, SDAx	—	—	400	pF	In I^2C mode

Note 1: Data in the "Typ" column is at 3.3V, +25°C unless otherwise stated. Parameters are for design guidance only and are not tested.

TABLE 33-25: A/D MODULE SPECIFICATIONS

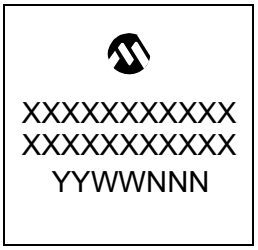
AC CHARACTERISTICS			Standard Operating Conditions: 2.0V to 3.6V (unless otherwise stated) Operating temperature -40°C ≤ TA ≤ +85°C for Industrial				
Param No.	**Symbol**	**Characteristic**	**Min.**	**Typ**	**Max.**	**Units**	**Conditions**
Device Supply							
AD01	AVDD	Module VDD Supply	Greater of: VDD – 0.3 or 2.2	—	Lesser of: VDD + 0.3 or 3.6	V	
AD02	AVSS	Module VSS Supply	VSS – 0.3	—	VSS + 0.3	V	
Reference Inputs							
AD05	VREFH	Reference Voltage High	AVSS + 1.7	—	AVDD	V	
AD06	VREFL	Reference Voltage Low	AVSS	—	AVDD – 1.7	V	
AD07	VREF	Absolute Reference Voltage	AVSS – 0.3	—	AVDD + 0.3	V	
Analog Inputs							
AD10	VINH-VINL	Full-Scale Input Span	VREFL	—	VREFH	V	**(Note 1)**
AD11	VIN	Absolute Input Voltage	AVSS – 0.3	—	AVDD + 0.3	V	
AD12	VINL	Absolute VINL Input Voltage	AVSS – 0.3	—	AVDD/3	V	
AD13		Leakage Current	—	±1.0	±610	nA	VINL = AVSS = VREFL = 0V, AVDD = VREFH = 3V, Source Impedance = 2.5 kΩ
AD17	RIN	Recommended Impedance of Analog Voltage Source	—	—	2.5K	Ω	10-bit
A/D Accuracy							
AD20B	Nr	Resolution	—	12	—	bits	
AD21B	INL	Integral Nonlinearity	—	±1	< ±2	LSb	VINL = AVSS = VREFL = 0V, AVDD = VREFH = 3V
AD22B	DNL	Differential Nonlinearity	—	—	< ±1	LSb	VINL = AVSS = VREFL = 0V, AVDD = VREFH = 3V
AD23B	GERR	Gain Error	—	±1	±4	LSb	VINL = AVSS = VREFL = 0V, AVDD = VREFH = 3V
AD24B	EOFF	Offset Error	—	±1	±2	LSb	VINL = AVSS = VREFL = 0V, AVDD = VREFH = 3V
AD25B		Monotonicity(1)	—	—	—	—	Guaranteed

Note 1: Measurements are taken with the external VREF+ and VREF- used as the A/D voltage reference.

34.0 PACKAGING INFORMATION

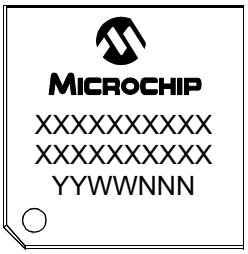
34.1 Package Marking Information

64-Lead QFN (9x9x0.9 mm)

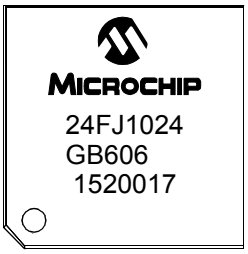


Example

64-Lead TQFP (10x10x1 mm)



Example



Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

NOTES: